

Ringing Subscriber Line Interface Circuit VE950 Series

Preliminary Data Sheet

Features

- Optimized to work with Broadcom BCM338x/ BCM339x Cable SoCs for short loop EMTA Applications
- Single Channel High Voltage Ringing SLIC that is functionally equivalent to the Le9541
- Software equivalent to Le9541
- Available in a 4x5 28-pin QFN that is cost optimized for single channel applications
- High Voltage High Bandwidth Design Supports 7-kHz Wide Band Applications
 - Up to -145 V ringing battery Le9551D
 - Up to -100 V ringing battery Le9551C
- Operation Control and Status Report through Serial Interface with Reset
- Supports GR909 Testing
- DC Loop Closure/Ring Trip/Thermal Shutdown
- Loop Start, Ring Trip, and Ring-Ground Detections with Two Thresholds
- Thermal Shutdown Protection with Hysteresis
- Test Load Switch Supports Integrated Test Algorithms

Description

The Le9551 is cost optimized for a single channel application. It is offered in a small 4x5 28-pin QFN. This device provides battery feed, ringing, and supervision on voice loops found in short-loop Cable applications. The Le9551 is optimized to interface to the Broadcom BCM338x or BCM339x families of Cable SoCs. It is software equivalent to the Microsemi Le9541, so no software change is needed from a current Le9541 design. Operational control and status report are communicated through a serial interface with reset. These devices support wide-band applications and GR909 testing.

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Ordering Information

Le9551CMQC 28-pin QFN Tray Le9551DMQC 28-pin QFN Tray

Le9551CMQCT 28-pin QFN Tape and Reel Le9551DMQCT 28-pin QFN Tape and Reel

All devices are in green package. The green package meets RoHS 2 Directive 2011/65/EC of the European Council to minimize the environmental impact of electrical equipment.

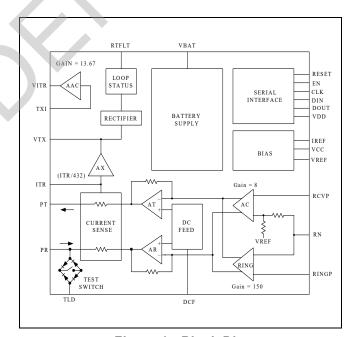


Figure 1 - Block Diagram

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Product Description

The Le9551 is a single channel device that is cost optimized for single channel applications. It provides the same functionality as the dual channel Le9540 or single channel Le9541 device. It provides battery feed, ringing, and supervision on short Plain Old Telephone Service (POTS) loops. Both devices are optimized to interface to Broadcom system-on-a-chip (SoC) device for cable modem applications.

Power Supplies

The Le9551 is powered by a Vcc for analog circuits, a VDD for the serial logic circuits and a VBAT for DC feed and power ringing. The maximum of VBAT is rated at -100 V for Le9551C and -145 V for Le9551D. The VBAT is expected to be a full tracking supply. The device depends on the tracking power supply to reduce the battery amplitude during off-hook conditions and by doing so may save overall operating power consumption. The VBAT should be no more negative than -100V for Le9551D other than in ringing mode. Also, when -145 V is used for ringing special care should be taken to prevent certain faults from happening, such as tip to ring, tip or ring to ground, or similar alike.

Operating States

The Le9551 device uses a voltage-feed-current-sense architecture. The device has active, scan, tip open, wink and disconnect operation states. Power ringing is also provided to the subscriber loop through amplification of a low-voltage input. The active forward state with the low (ILL) DC current limit and the test switch turned off is the default power up state.

Active

There are three active states: Active Forward, Active Reverse and Active Forward ICV.

In the Active Forward state the DC feed voltage on PT is positive with respect to the voltage on PR. In the Active Reverse state the DC feed voltage on PT is negative with respect to the voltage on PR.

In the Active Forward ICV state the PT voltage is forced to be near -20V. The channel will be operating with an Increased Common mode Voltage (ICV).

The DC feed current is limited and can be programmed to either ILL or ILH. There is in the order of a 10 k Ω slope to the I/V characteristic in the current-limit region; thus, once in current limit, the actual loop current will increase slightly as loop length decreases.

For AC operation the Le9551 supports off-hook talk mode and on-hook transmission mode as may be required during the quiet interval of ringing. The overhead is about 6 to 8 V, allowing for on-hook transmission of an undistorted signal of 3.14 dBm into 900Ω , or 500 mV of meter pulse.

Scan

Scan is a simple low-power operation state. It is designed primarily for on hook operation. It provides forward DC feed with the voltage on PT positive with respect to the voltage on PR. The loop closure detector is active. The DC feed current is limited and fixed. The AC transmission path and on-hook transmission are not active.

Tip Open

The Tip Open state is the Scan state with high impedance into PT.

Wink

The Wink state is an Active state but the voltages on PT and PR are forced to be the same and near ground.

Disconnect

Both PT and PR are in high impedance.

Ringing

In the Ringing state the signals on RINGP and RN are amplified and provided to the tip/ring pair as the power ringing signal. The signals on RINGP and RN may be a sine wave or a filtered square wave to produce a sine wave or trapezoidal output. A DC offset may also be applied.

The signals on RINGP and RN are desirable to be referenced to VREF or near VREF potential for maximum dynamic ranges on the inputs.

Communication Interface

A serial interface is used for device operational control and for device status reporting. For operational control through DIN, the operation state, dc current limit and test load switch operation can be set. The upstream status reporting on DOUT are loop closure, ring trip and thermal shutdown. There are two loop closure outputs related to two detection thresholds, two ring trip detection outputs related to two detection thresholds, and one thermal shutdown indications.

The serial interface has a RESET which is active low. When the RESET pin is a logic 0 the device will enter its default state of active forward with the low (ILL) dc current limit and the test switch turned off. The RESET pin has an internal pull down.

Package

Le9551 is available in a 28-pin QFN package (4mm x 5mm).

Protection

A battery referenced protection device should reference to VBAT. Connect the gate of the battery referenced protection device to VBAT.

Thermal

The device is packaged in a QFN with an exposed pad. The Exposed Pad must be connected to a ground plane on the printed circuit board for thermal conduction. Also, the internal analog grounds and battery grounds are connected to the exposed pad, as well as to the GND pin. The single GND pin may not be sufficient for peak current return. The ground plane to which the exposed pad connects is used as analog signal ground and battery ground.

In case of reaching the thermal shutdown temperature, the channel will automatically enter an all off state. Upon cooling, the device will re-enter the state contained in the serial interface control registers. Hysteresis is built in to prevent fast oscillation. This is a self protection operation. Thermal shutdown will not cause performance degradation once the device goes back to normal operation.

Connection Diagram

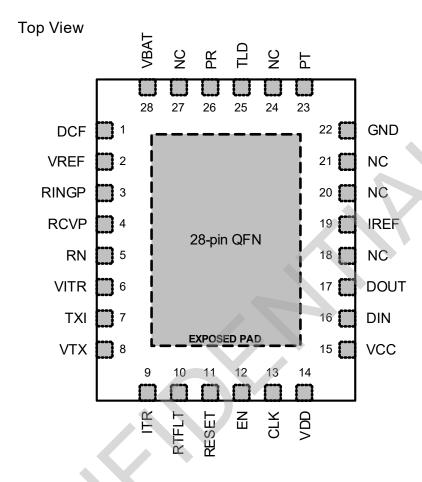


Figure 2 - 28 Pin 4x5 QFN

Note: Exposed pad should be connected to the ground plane for electrical connection and thermal conduction.

Pin Descriptions

Pin Name	Type	Description
VITR	Output	Transmit AC Output Voltage. Output of internal AAC amplifier. This output is a voltage that is directly proportional to the differential AC tip/ring current.
RCVP	Input	Receive AC Signal Input (Non inverting). This high-impedance input controls the AC differential voltage on tip and ring, for voice in Active states. This node is a floating input.
RN	Input	Receive AC Signal Input and Power Ringing Signal Input (Inverting). In Active States this input, with reduced gain and referenced to VREF, is paired with RCVP for voice transmission. In Ringing State this input is paired with RINGP with the same gain as that of RINGP.
RINGP	Input	Power Ring Signal Input (Non inverting). Couple to a sine wave or lower crest factor low-voltage ring signal. The input here is amplified to provide the full power ring signal at tip and ring. This signal may be applied continuously, even during non-ringing states.
DCF	Input	Filter Capacitor. Connect a capacitor from this node to ground.
RTFLT	Input	Ring Trip Filter. Connect a capacitor to ground to filter the ring trip circuit to prevent spurious responses. A single-pole filter is needed.
VREF	Output	SLIC Device Internal Reference Voltage. Output of internal 1.5 V reference voltage.
IREF	Input	SLIC Device Internal Reference Current. Connect a 49.9 $k\Omega$ resistor to low noise analog ground.
VCC	Power	Analog Power Supply. 3.3 V typical.
VDD	Power	Digital Power Supply. 3.3V typical.
VBAT	Power	Battery Supply. User adjusted supply per SLIC operation state and device grade.
PT	Input/ Output	Protected Tip. The output drive of the tip amplifier and input to the loop-sensing circuit. Connect to loop through over-voltage and over-current protection.
PR	Input/ Output	Protected Ring. The output drive of the ring amplifier and input to the loop sensing circuit. Connect to loop through over-voltage and over-current protection.
ITR	Input	Transmit Gain. Input to AX amplifier. Connect a 6.49 k Ω resistor from this node to VTX to set transmit gain of 205V/A.
VTX	Output	DC and AC Output Voltage. Output of internal AX amplifier. The voltage at this pin is directly proportional to the differential tip/ring current.
TXI	Input	AC/DC Separation. Input to internal AAC amplifier. Connect a capacitor from this pin to VTX.
TLD	Input	Test Load. A test load may be connected to this pin.
RESET	Input	Reset. When low it resets the SLIC and both channels will be in default mode. It comes with internal $100kΩ$ pull down.
EN	Input	Enable. Activate the serial interface operations.
CLK	Input	Clock for the Serial Data Transmission. Clock that runs the serial interface.
DIN	Input	Data Input. Data inputs of the serial interface.
DOUT	Output	Data Output. Data outputs of the serial interface.

Pin Name	Туре	Description
NC		No Connect. Internally not connected.
GND	GND	Ground. Use together with the exposed pad as ground return.
Exposed Pad		Thermal and Circuit Ground . Connect to a ground plane on the printed circuit board for thermal conduction and electrical connection for ground return.



Absolute Maximum Ratings

Stresses above those listed under *Absolute Maximum Ratings* can cause permanent device failure. Functionality at or above these limits is not implied. Exposure to absolute maximum ratings for extended periods may affect device reliability. T_A = 25 °C

Parameter	Symbol	Min.	Max.	Unit
DC Supply (Vcc, VDD)	Vcc, Vdd	-0.4	4.0	V
Battery Supply (V _{BAT}) (Le9551C, Le9551D Non-Ringing)	VBAT	–110	GND	V
Battery Supply (V _{BAT}) (Le9551D Ringing)	VBAT	–155 + Vcc	GND	V
Logic Input Voltage		-0.4	VDD + 0.5	V
Logic Output Voltage		-0.4	VDD+ 0.5	V
Operating Temperature Range		-40	125	°C
Storage Temperature Range		-40	150	°C
Relative Humidity Range		5	95	%
PT or PR Fault Voltage (DC)	VPT, VPR	V _{BAT} – 5	3	V
PT or PR Fault Voltage (10 x 1000 μs)	VPT, VPR	V _{BAT} – 15	15	V
ESD Immunity (Human Body Model)			JESD22 Class 1C compliant	
			compliant	

Thermal Resistance

The thermal performance of a thermally enhanced package is assured through optimized printed circuit board layout. Specified performance requires that the exposed thermal pad be soldered to an equally sized exposed copper surface, which, in turn, conducts heat through multiple vias to a large internal copper plane. Thermal performance depends on number of PCB layers and the size of copper area. Continuous operation above 145°C junction temperature may degrade device reliability.

The typical thermal protection shutdown (TjC) temperature is 190°C, with minimum at 175°C.

Package Assembly

Green package devices are assembled with enhanced environmental compatible lead-free, halogen-free, and antimony-free materials. The leads possess a matte-tin plating which is compatible with conventional board assembly processes or newer lead-free board assembly processes. The peak soldering temperature should not exceed 245°C during printed circuit board assembly.

Refer to IPC/JEDEC J-Std-020B Table 5-2 for the recommended solder reflow temperature profile.

Operating Ranges

Environmental Ranges

Microsemi guarantees the performance of this device over commercial (0 to 70°C) and industrial (-40 to 85°C) temperature ranges by conducting electrical characterization over each range and by conducting a production test with single insertion coupled to periodic sampling. These characterization and test procedures comply with section 4.6.2 of Bellcore GR-357-CORE Component Reliability Assurance Requirements for Telecommunications Equipment.

Ambient Temperature	-40° C < T _A < +85° C
Ambient Relative Humidity	5 to 95%

Electrical Ranges

Parameter	Min.	Тур.	Max.	Unit
3.3 V DC Supplies (Vcc, VDD)	3.13	3.3	3.47	V
Office Battery Supply (VBAT) (Le9551C)	-100 ¹		-12	V
Office Battery Supply (VBAT) (Le9551D)	-100 ¹		-12	V
Office Battery Supply (VBAT) (Le9551D) (during ringing only)	-145 ¹		-12	V

Note:

^{1.} Full tracking supply is expected during off hook and ringing operations. These maximum values may be the maximum on hook voltage or the peak voltage during ringing.

Electrical Characteristics

Supply Currents

On-hook with no loop current. VDD = Vcc = 3.3 V. Test switch is off.

Parameter	Min.	Тур.	Max.	Unit
Scan state, VBAT= –60 V:				
lvcc	_	3.63	4.63	mA
I _{VBAT}	_	0.19	0.22	mA
Active state, Forward and Reverse, VBAT= -60 V:				
lvcc	_	4.70	5.68	mA
I _{VBAT}	_	1.24	1.36	mA
Active state, Forward ICV state, VBAT= -60 V:				
lvcc	_	4.83	5.86	mA
I _{VBAT}	_	1.33	1.47	mA
Active state, Forward and Reverse, VBAT= –21 V:			-	
lvcc	_	4.69	5.68	mA
I _{VBAT}		1.22	1.33	mA
Disconnect state, VBAT= -60 V				
lvcc		2.99	3.98	mA
I _{VBAT}	\	0.02	0.04	mA
Tip Open state, VBAT= -60 V				
vcc) —	3.32	4.28	mA
I _{VBAT}	_	0.17	0.20	mA
Wink state, VBAT= –60 V				
lvcc	_	4.8	5.8	mA
I _{VBAT}	_	1.3	1.4	mA
Ring state, no load, VBAT= -100 V (Le9551C)				
vcc	_	4.7	5.6	mA
I _{VBAT}	_	1.9	2.1	mA
Ring state, no load, VBAT= -145 V (Le9551D)				
lvcc	_	4.7	5.6	mA
I _{VBAT}	_	2.0	2.3	mA
All operation states				
I_{VDD}	-	1.9	2.2	mA

Power Dissipation

On-hook with no loop current. VDD = Vcc = 3.3 V. Test switch is off.

Parameter	Min.	Тур.	Max.	Unit
Scan state, V _{BAT} = -60 V	_	30	36	mW
Active state, Forward/Reverse, V _{BAT} = -60 V	_	96	107	mW
Active state, Forward ICV V _{BAT} = -60 V	_	102	115	mW
Active state, Forward/Reverse, V _{BAT} = –21 V	_	47	54	mW
Disconnect state, V _{BAT} = -60 V	_	17	23	mW
Tip Open state, V _{BAT} = –60 V	_	27	1	mW
Wink state, V _{BAT} = -60 V	_	100	\-\	mW
Ring state, no load, V _{BAT} = -100 V (Le9551C)	_	211	236	mW
Ring state, no load, V _{BAT} = -145 V (Le9551D)	_	312	359	mW

Line Characteristics

Unless specified the test condition is specified in Figure 5, "Le9551 Basic Test Circuit" on page 23.

Typical values are characteristic of the device and are the result of engineering evaluations. Typical values are for information purposes only and are not a part of the testing requirements. Minimum and maximum values apply across the operating temperature range and the entire battery range unless otherwise specified. Typical is defined as TA=25° C, VDD = Vcc = 3.3V, VBAT= -60V for scan and disconnect state, -30V for active states, -100V for ringing state (for Le9551C), -145V for ringing state (for Le9551D). Test Switch is OFF.

Parameter	Min.	Тур.	Max.	Unit
Tip or Ring Drive Current = DC + Longitudinal + Signal Currents, Active states ¹	105	_	_	mApk
Tip or Ring Drive Current = Ringing + Longitudinal, Ring state	65	7		
Signal Current, Active states ¹	10	Y		
Longitudinal Current Capability per Wire (Longitudinal current is independent of DC loop current.) ¹	8.5	15	_	mArms
Ringing Current (Tip-Ring Ringing Load 1386 Ω + 40 μ F) ¹	29	_	_	
DC Loop Current Limit, Active States (Tip-Ring DC Load 300 Ω):				
ILL	22.5	23.5	24.5	mA
ILH	38	40	42	mA
DC Loop Current Limit, Scan State (Tip-Ring DC Load 300 Ω)	_	30	_	mA
DC Loop Current Limit, Tip Open State (300 Ω Ring to ground)	_	30	_	mA
DC Feed Resistance (at PT-PR, Active states, non-current limit)	_	40	_	Ω
Open Loop Overhead Voltages:				
Scan state: (VTIP – VRING) – VBAT	2	3.6	4.5	V
Active state: (VTIP – VRING) – VBAT	5.75	7.4	8.5	V
Wink state: VTIP , VRING		0.7	1.0	V
Ring state: VTIP , VRING – VBAT	_	3.0	_	V
Open Loop Voltage:				
Active Forward ICV state: PT	-23.0	-21.6	-20.0	V
Loop Closure Detection Threshold:				
Active/Scan states (LCL)	10	11	12	mA
Active/Scan states (LCH)	14	15	16	mA
Tip Open state (LCL)	8.5	11	12.5	mA
Tip Open state (LCH)	13.5	15	16.5	mA
Loop Closure Detection Threshold Hysteresis ² :				
Active/Scan/Tip Open states	_	2.2	_	mA

Table 1 - Two-Wire Port

Parameter	Min.	Тур.	Max.	Unit
Longitudinal to Metallic Balance at Tip/Ring:				
Test Method: Q552 (11/96) Section 2.1.2 and <i>IEEE</i> ® 455:				
200 Hz to 3.4 kHz ³	52	_		dB
Metallic to Longitudinal (HARM) Balance ⁴ :				
100 Hz to 4000 Hz	40		_	dB
PSRR 500 Hz to 3000 Hz (Active Forward/Reverse) ¹ :				
VBAT	45	-	_	dB
Vcc	25	30		dB
VDD	25	30		dB

Note 1: This parameter is not tested in production. It is guaranteed by design and device characterization.

Note 2: Refer to "Loop Closure and Ring Trip Detection Thresholds with Hysteresis".

Note 3: Tested at 1kHz.

Note 4: Tested with DC signals.

Table 1 - Two-Wire Port

Parameter	Min.	Тур.	Max.	Unit
TXI				
Input impedance	_	100	_	kΩ
VTX and VITR				
Output Offset (VTX)	-10	0	10	mV
Output Offset (VITR)	_	_	100	mV
Output Drive Current (VTX) (sinking or sourcing)	300	_	_	μA
Output Drive Current (VITR) (sinking or sourcing)	10	_	_	μA
Output Voltage Swing:				
Maximum (VTX, VITR)	0	- 6	Vcc	V
Minimum (VTX)	+ 0.25	_	Vcc - 0.5	V
Minimum (VITR)	+ 0.35		Vcc – 0.4	V
Output Short-circuit Current (sinking or sourcing)	_		50	mA
Output Load Resistance ¹	10		_	kΩ
Output Load Capacitance ¹	_	20	_	pF
RN and RCVP (Active States):				
Input Voltage (Vcc = 3.3 V)				
RCVP	0	_2	$V_{cc} - 0.3$	V
RN	0	VREF	$V_{cc} - 0.3$	V
Input Bias Current				
RCVP (sinking)	_	0.12	_	μA
RN (sinking ³ or sourcing ⁵)	_	0^{4}	35	μA
Differential PT/PR Current Sense (RTFLT) ³ :				
Gain (PT/PR to RTFLT)	_	30	_	V/A
Total Harmonic Distortion (200 Hz—4 kHz) ¹ :				
Off-hook	_	_	0.3	%
On-hook	_	_	1.0	%
Transmit Gain (f = 1004 Hz, 1020 Hz) ⁶				
PT/PR Current to VITR	-211	-205	-199	V/A
Receive Gain, f = 1004 Hz, 1020 Hz Open Loop				
RCVP to PT/PR	7.76	8.00	8.24	V/V
RN to PT/PR	3.34	3.44	3.54	V/V

Table 2 - Analog Pin Characteristics

Parameter	Min.	Тур.	Max.	Unit
Gain vs. Frequency (transmit and receive), 600 Ω				
Termination, 1004 Hz, 1020 Hz Reference ¹ :				
200 Hz to 300 Hz	-0.3	0	0.05	
300 Hz to 3.4 kHz	-0.05	0	0.05	dB
3.4 kHz to 20 kHz	-3.0	0	0.05	
20 kHz to 266 kHz	_	_	2.0	
Gain vs. Level, 600 Ω Termination, Transmit +3dBm, Receive 0dBm Reference ¹ :				
-55 dB to +3.0 dB	-0.05	0	0.05	dB
Idle-channel Noise (Tip/Ring), 600 Ω Termination:				
C-Message	_	8	13	dBrnC
Psophometric ¹	_	-82	–77	dBrnp
3 kHz Flat ¹			20	dBrn

Note 1: This parameter is not tested in production. It is guaranteed by design and device characterization.

Note 2: The RCVP input is floating. However, referencing it to VREF is recommended since RN is internally referenced to VREF.

Note 3: RN = 0V Note 4: RN = VREF Note 5: RN = Vcc-0.3V

VITR transconductance depends on the resistor from ITR to VTX. This gain assumes an ideal 6.49 k Ω , (the recommended value). Positive current is defined as the differential current flowing from PT to PR. Note 6:

Table 2 - Analog Pin Characteristics

Parameter	Min.	Тур.	Max.	Unit		
RINGP/RN (Ringing State): Input Voltage Swing	0		Vcc	V		
Ring Signal Isolation: PT/PR to VITR Ringing state	_	60	_	dB		
Ring Signal Isolation: RINGP to PT/PR Non-ringing state	_	80	_	dB		
Ring Signal Distortion ¹ :						
For Le9551C						
V _{BAT} = -100 V, RINGP/RN = 0.6 Vpp, Open Loop or 5 REN (1386Ω + 40μ F) with DC loop 0 to 100Ω	_	3		%		
For Le9551D						
V _{BAT} = -145 V, RINGP/RN = 0.9 Vpp, Open Loop or 5 REN (1386Ω + 40μF) with DC loop 0 to 100Ω		3	_	%		
Differential Gain RINGP/RN to PT/PR						
For Le9551C						
VBAT = -100 V, RINGP/RN = 0.6 Vpp, Open Loop	124	130	136	V/V		
For Le9551D						
VBAT = -145 V, RINGP/RN = 0.9 Vpp, Open Loop	124	130	136	V/V		
Note 1: This parameter is not tested in production. It is guaranteed by design and device characterization.						

Table 3 - Ringing Parameters

Parameter	Min.	Тур.	Max.	Unit
Ring Trip (RTL):	50.5	52.5	54.5	mA
Ring Trip (RTH):	59.5	62.0	64.5	mA
Trip Time (f = 20 Hz) ¹	_	_	100	ms
Hysteresis (Relative to RTL or RTH) ^{1, 2}	_	1/3	_	

Note 1: This parameter is not tested in production. It is guaranteed by design and device characterization.

Note 2: Refer to "Loop Closure and Ring Trip Detection Thresholds with Hysteresis".

Table 4 - Ring Trip

Item	Condition	Min.	Тур.	Max.	Unit.				
Test Switch	ON-Resistance, (V(25 mA) – V(20 mA)) / 5 mA	10	19	30	Ω				
	On-Voltage drop at ±20 mA ¹	-3	_	+3	V				
	Off-state Leakage Current (sinking or sourcing)	_	_	5	μA				
Note 1: Additio	Note 1: Additional 10% variations to the minimum and maximum limits at -40° C.								

Table 5 - Test Switch

Serial Interface Characteristics

The electrical characteristics of the serial interface are shown in <u>Table 6</u>.

Parameter	Symbol	Min.	Тур.	Max.	Unit
Input Voltages (DIN, CLK, EN)					
Low Level	VIL			8.0	V
High Level	ViH	2.0	_	VDD	V
Input Current (DIN, CLK, EN)					
Low Level (ground) (sourcing)	lıL			60	μΑ
High Level (VDD) (sinking)	I _{IH}			1	μΑ
Output Voltages (DOUT)			-		
Low Level	Vol			0.55	V
High Level	Vон	2.0		2.6 ¹	V
Rising/Falling Time (DOUT) (20% to 80%) with 20pF load	T _R , T _F			100 ²	ns
RESET High Current (at 2.5V) (sinking)	Ін			40	μΑ

Note 1: Depending on the characteristic of the input that DOUT will be driving an external pull down resistor may be required to keep DOUT below the specified voltage for speedy operation.

Table 6 - Serial Interface Electrical Characteristics

The serial interface timing characteristics are shown in Figure 3. The details are in Table 7.

Symbol	Description	Min.	Тур.	Max.	Unit
1	CLK Period	1			μs
2	CLK falling to ENable going high	0			ns
3	ENable going high to CLK rising	300			ns
4	CLK falling to ENable going low	0			ns
5	ENable going low to CLK rising	170			ns
6	Data ready	200			ns
7	Data hold	200			ns
8	Enable rising to DOUT0 data available			420	ns
9	CLK rising to DOUT1+ data available			350	ns
10	CLK, EN rising time (20% to 80%)			25	ns
11	CLK, EN falling time (20% to 80%)			25	ns

Note that the parameters in table 7 are not tested in production. They are guaranteed by design and device characterization.

Table 7 - Serial Interface Timing Characteristics

Note 2: This parameter is not tested in production. It is guaranteed by design and device characterization.

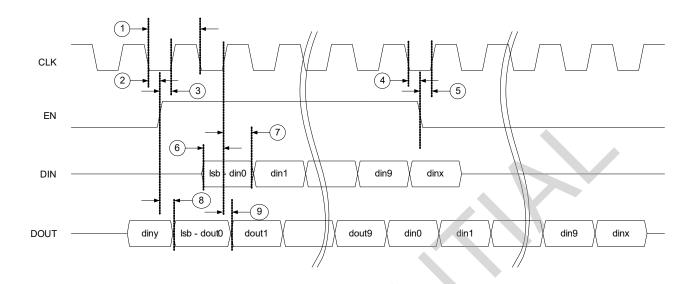


Figure 3 - Serial Interface Timing Diagram

Serial Interface Operations and Definitions

The serial interface has a 10-bit serial shift register and a 10-bit parallel data latch register that controls the SLIC operations. The timing diagram is shown in <u>Figure 3</u>. The logic diagram is shown in <u>Figure 4</u>. The detailed definitions are in shown in <u>Table 8</u> and <u>Table 9</u>. Of the 10 control input bits, d3/d4/d5/d7/d9 can be 0 or 1, although 11100 are recommended. Of the 10 status output bits, b5/d6/d7/d8/d9 should be ignored, although 11111 are expected.

Serial Interface Operations

The operation of the serial interface can be described in the following four modes, RESET High Enable No Transition, RESET High Enable Going High, RESET High Enable Going Low and RESET Low.

RESET High Enable No Transition

When RESET is high and there is no recent low-to-high transition on Enable the content in the shift register is continuously moving from DIN to DOUT by CLK. DOUT is continuously repeating DIN delayed by 10 CLK cycles.

Regardless of the CLK status, device state changes are not loaded with the Enable state held static. Data already loaded to the shift register may be reloaded without disrupting the SLIC channel line state.

RESET High Enable Going High

When RESET is high a low-to-high transition on Enable loads the parallel status bits into the shift register, overwriting the previous 10 bit content in the shift register. The first lsb of the 10-bit device status word will immediately appear on the DOUT pin. Subsequent clock edges will continue to shift the status word out until all 10 bits have been presented, as which time the DOUT will return to repeat DIN delayed by 10 CLK cycles.

The second rising edge of CLK after Enable goes high CLK will clock in (new) data from DIN.

RESET High Enable Going Low

When RESET is high a high-to-low transition on Enable latches control bits from the serial shift register (with the content at that instant) into the SLIC parallel control register and immediately take effect.

New control data transactions are only triggered by such a transition on the Enable pin.

RESET Low

When RESET is low it over-writes the content in the SLIC parallel control register and set the control register to "00000 00000". The SLIC is put into a default mode of active forward with ILL current limit and the test switch off. When RESET is low the operation of Enable is frozen such that the contents in the serial shift register will not be loaded into the SLIC parallel control registers and the status bits will not be loaded into the serial shift register. Asserting RESET does not clear the contents of the shift register. The content in the serial shift register will move from DIN to DOUT by CLK when RESET is low and Enable is low. If Enable is high during the period when RESET is low the content in the shift register will not change.

The RESET function is not included in Figure 4.

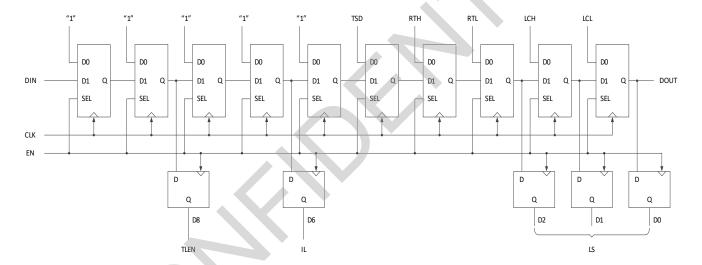


Figure 4 - Serial Interface Logic Diagram

Bit Assignments

The bit assignments for DIN are defined in Table 8.

Note that bits d3/d4/d5/d7/d9 can be 0 or 1.

d0	d1	d2	d3	d4	d5	d6	d7	d8	d9
LS		1/0	1/0	1/0	IL	1/0	TLEN	1/0	

Table 8 - Serial Interface Input Arrangements

The bit assignments for DOUT are defined in Table 9. Bits d5/d6/d7/d8/d9 should be ignored.

d0	d1	d2	d3	d4	d5	d6	d7	d8	d9
LCL	LCH	RTL	RTH	TSD	1	1	1	1	1

Table 9 - Serial Interface Output Arrangements

Line State (LS)

000: Active Forward (Normal)

001: Active Forward ICV (Increased Common mode Voltage)

010: Active Reverse (Normal)

011: Wink

110: Tip Open

100: Scan

101: Ringing

111: Disconnect

(in the sequence of d0/d1/d2 so scan state d0 = 1)

DC Current Limit (IL)

0: DC current limit is set to be ILL

1: DC current limit is set to be ILH

Test Load ENable (TLEN)

0: test load switch disabled and the test load is not turned on

1: test load switch enabled and the test load is turned on

Thermal ShutDown (TSD)

0: thermal shutdown

1: no thermal shutdown

Loop Closure with Low Detection Threshold (LCL)

0: dc loop current is greater than LCL threshold1

1: dc loop current is smaller than LCL threshold¹

Loop Closure with High Detection Threshold (LCH)

0: dc loop current is greater than LCH threshold¹

1: dc loop current is smaller than LCH threshold¹

Ring Trip with Low Detection Threshold (RTL)

0: rectified and filtered loop current is greater than RTL threshold¹

1: rectified and filtered loop current is smaller than RTL threshold¹

Ring Trip with High Detection Threshold (RTH)

0: rectified and filtered loop current is greater than RTH threshold¹

1: rectified and filtered loop current is smaller than RTH threshold¹

Note: 1. Refer to "Loop Closure and Ring Trip Detection Thresholds with Hysteresis" for additional details.



Test Circuit

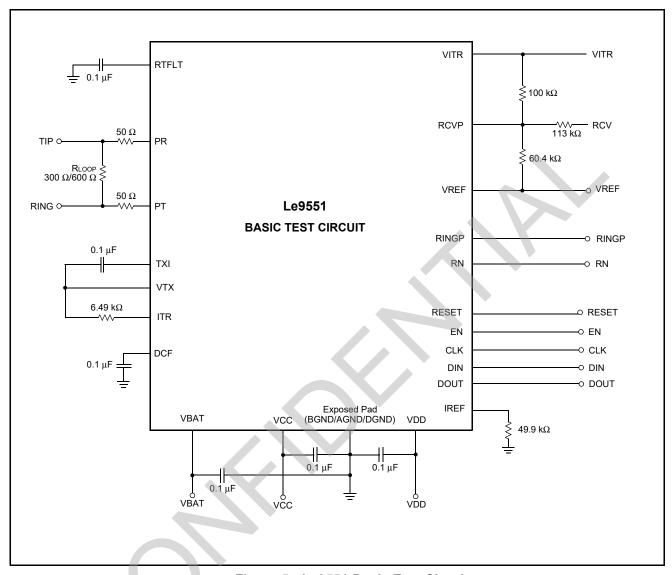


Figure 5 - Le9551 Basic Test Circuit

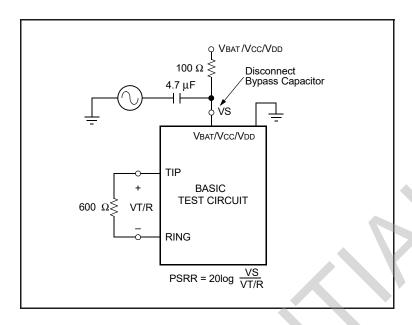


Figure 6 - Metallic PSRR

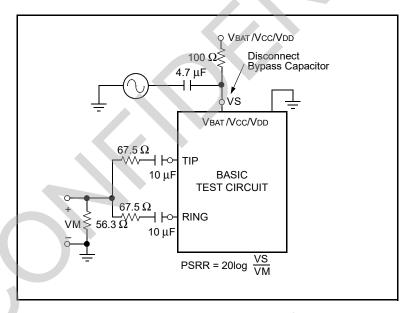


Figure 7 - Longitudinal PSRR

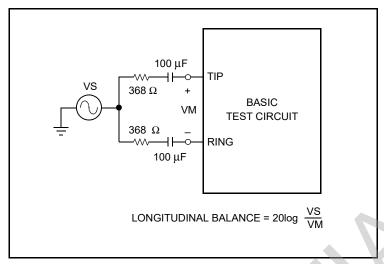


Figure 8 - Longitudinal Balance

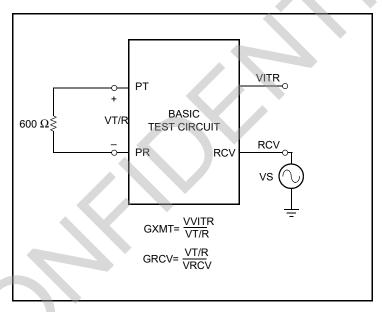


Figure 9 - AC Gains

Applications

In-rush Control

In the Active or Scan states there will be a transient response of the current-limit circuit upon an on- to off-hook transition that is described in the table below.

Parameter	Value	Unit
DC Loop Current: R_{LOOP} = 100 Ω , On- to Off-hook Transition time < 5 ms	ILIM + 60	mA
DC Loop Current: R_{LOOP} = 100 Ω , On- to Off-hook Transition time < 50 ms	ILIM + 20	mA
DC Loop Current: R_{LOOP} = 100 Ω , On- to Off-hook Transition time < 300 ms	ILIM	mA

Table 10 - Typical Active or Scan state On-Hook to Off-Hook Tip/Ring Current-Limit Transient Response

Loop Closure and Ring Trip Detection Thresholds with Hysteresis

Both loop closure and ring trip detections have a programmable threshold and hysteresis. The detection threshold is the point where the current is large enough for loop closure or ring trip to be detected. Once loop closure or ring trip is detected lowering the current will not immediately clear the detection until the current is below the programmed threshold minus the hysteresis.

For loop closure detection the "current" is the rectified loop current. For ring trip detection the "current" is the rectified and filtered loop current.

Figure 10 shows the characteristic graphically.

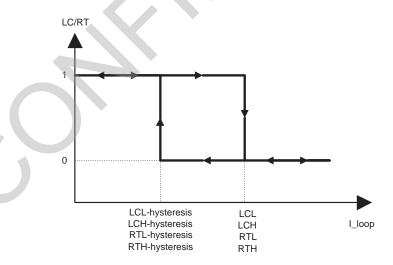


Figure 10 - Detection Thresholds with Hysteresis

All detectors are active regardless of the operational state.

Design Examples

The following circuit shows the SLIC interface to the Broadcom BCM338x and BCM3390. This circuit has a natural 703- Ω AC termination impedance. The Broadcom IC has programmable registers to modify the external 703- Ω termination to any other real or complex terminations, as well as to set transmit and receive gains, and other AC parameters, such as parameters for 7kHz wide-band applications. The Broadcom IC also drives ringing inputs, sets SLIC operation states, and monitors line status. The voltage of the battery supply to the SLIC VBAT is expected to be properly set and may vary depending upon SLIC operational states. The ringing maybe driven by the same voice outputs. The details of the protection are not shown. A complete reference design is available from Broadcom.

Please note the Required Components Block may not 100% align with the Broadcom reference design. These are requirements from Microsemi above and beyond the Broadcom reference design.

Contact your Microsemi account representative with questions or for technical assistance.

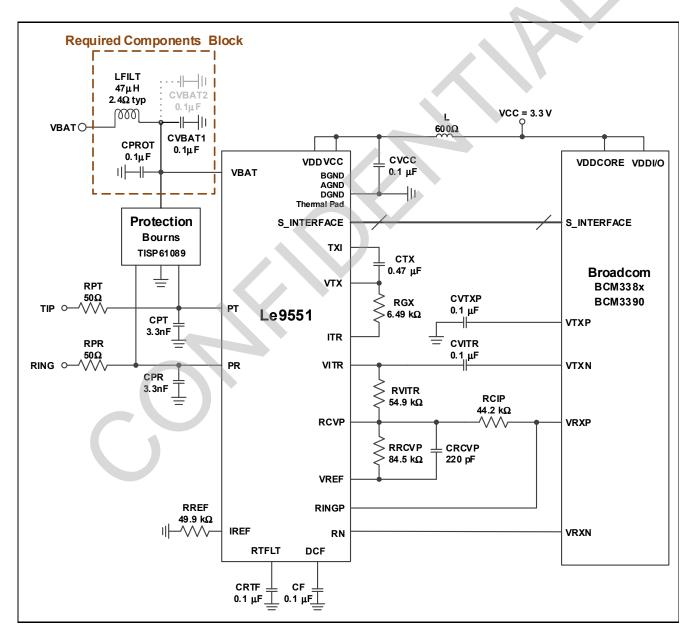


Figure 11 - Reference Schematic Interfacing Broadcom Codec

Application Circuit Parts List

The following parts list is for the Microsemi Le9551 SLIC device and Broadcom BCM338x or BCM3390 SoC.

Type	Value	Tolerance	Rating	Comments
Inductor	47 μH 2.0 DCR	20% minimum DCR	70 mA	Taiyo Yuden LB 2016T470M or equivalent
Capacitor	0.1 μF	20%	See Note 4	Ceramic X7R 100V use 0805 250V use 1206
Capacitor	0.1 μF	20%	See Note 4	DNP
Capacitor	0.1 μF	20%	See Note 4	Ceramic X7R 100V use 0805 250V use 1206
				Bourns TISP61089 or equivalent.
Capacitor	0.1 μF	20%	10 V	Ceramic bypass capacitor.
	600 Ω, <i>Murata</i> [®] BLM11A601SPB	_		Ferrite Bead for filtering.
Resistor	49.9 kΩ	1%	1/16 W	Sets internal reference current
SLIC	_			Single-channel SLIC device.
Resistor	50 Ω ⁷	20% absolute	Fusible or PTC	Protection resistor.
Resistor	50 Ω ⁷	1% mismatch	Fusible or PTC	Protection resistor.
Capacitor	0.1 μF	20%	10 V	Ring trip filter capacitor.
Capacitor	0.1 μF	20%	100 V	DC feed filter capacitor.
Resistor	6.49 kΩ	1%	1/16 W	Sets trans-impedance.
Capacitor	0.47 μF	20%	10 V	AC/DC separation.
Capacitor	0.1 μF	20%	10 V	DC blocking capacitor
Resistor	54.9 kΩ	1%	1/16 W	AC interface.
Resistor	44.2kΩ	1%	1/16 W	AC interface.
Resistor	84.5 kΩ	1%	1/16 W	AC interface.
Capacitor	220 pF	20%	10 V	AC interface.
Capacitor	0.1 μF	20%	10 V	AC interface.
Capacitor	3.3 nF ²	20%	200V	EMC
Capacitor	3.3 nF ²	20%	200V	EMC
	Capacitor Capacitor Capacitor Capacitor Capacitor Resistor Resistor Capacitor Capacitor Capacitor Capacitor Resistor Capacitor	$\begin{array}{c c} 2.0 \ \text{DCR} \\ \hline \text{Capacitor} & 0.1 \ \mu\text{F} \\ \hline \\ \hline \text{Capacitor} & 0.1 \ \mu\text{F} \\ \hline \\ \hline \text{Capacitor} & 0.1 \ \mu\text{F} \\ \hline \\ \hline \\ \hline \text{Capacitor} & 0.1 \ \mu\text{F} \\ \hline \\ $	Capacitor 2.0DCR minimum DCR Capacitor $0.1 \mu\text{F}$ 20% Capacitor $0.1 \mu\text{F}$ 20% Capacitor $0.1 \mu\text{F}$ 20% Capacitor $0.1 \mu\text{F}$ 20% BLM11A601SPB — — Resistor $49.9 \text{k}\Omega$ 1% SLIC — — Resistor $50 \Omega^7$ 20% absolute Resistor $50 \Omega^7$ 1% mismatch Capacitor $0.1 \mu\text{F}$ 20% Capacitor $0.1 \mu\text{F}$ 20% Capacitor $0.1 \mu\text{F}$ 20% Capacitor $0.47 \mu\text{F}$ 20% Capacitor $0.47 \mu\text{F}$ 20% Capacitor $0.1 \mu\text{F}$ 20% Resistor $54.9 \text{k}\Omega$ 1% Resistor $54.9 \text{k}\Omega$ 1% Resistor $54.9 \text{k}\Omega$ 1% Resistor $54.9 \text{k}\Omega$ 1% Capacitor 220p <td>$\begin{array}{c ccccccccccccccccccccccccccccccccccc$</td>	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$

Note 1: Component is in the "Required Component Block". Components and associated notes in the "Required Components Block" are Microsemi device requirements that may be in addition to the Broadcom Reference Design.

Note 2: Inductor improves Conducted Emissions response. Inductor requires 2.0 ohm minimum DCR.

Note 3: A 20 ohm resistor may be used instead of the Inductor if a reduced Conducted Emissions response is acceptable. If a resistor is substituted CPROT is optional.

Note 4: Capacitor rating must be consistent with maximum supply voltage from the switching regulator.

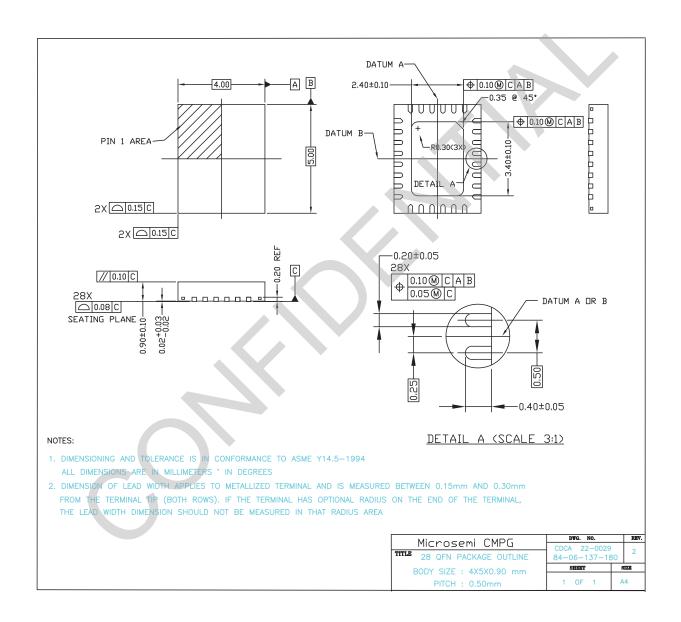
Note 5: If a 100V rated capacitor is used for CBAT1, then CPROT is required and may be 100V. If a 250V rated capacitor is used for CBAT1, then CPROT is optional.

Note 6: Do Not Populate. Include footprint in PCB design for additional filtering if required.

Note 7: Minimum 40Ω required for loop stability.

Physical Dimensions

28-pin QFN



Revision History

Version 1

· Initial Issue

Version 1 to Version 2

- Added device requirements in the Required Component Block in Figure 11 and "Application Circuit Parts List" on page 28
- Change Document Number to reflect use of the Microsemi Document Management System

Version 2 to Version 3

- · Updated the document logo.
- Corrected Figure sequence. In Version 2 there were two figures that were both Figure 1.
- Table 2, on page 16, Gain vs. Level, updated "0dBV Reference" to "Transmit +3dBm and Receive 0dBm Reference".
- Upgraded the <u>Physical Dimensions</u>, on page 29 so the drawing has the proper resolution.

Version 3 to Version 4

Updated Loop Closure Detection Threshold for Tip Open state (LCL) in Table 1 on page 13. The specification for the minimum value is changed from 9.5mA to 8.5mA.

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